

Serial No. 10/633,952

Amendments to the Specification

Please amend the first subheading and paragraph of text (lines 3-11 of page 1) of the specification as follows:

Cross-Reference to ~~Provisional~~ Related Applications

This application is a continuation of and claims priority from Application Serial No. 09/850,687, filed May 7, 2001, now U.S. Patent 6,602,764, which in turn claims the benefit of Provisional Application Serial No. 60/109,674, filed November 24, 1998 entitled *Methods for Growing Low Defect Gallium Nitride Semiconductor Layers on Silicon or Silicon Containing Wafers Using a Conversion and Lateral Epitaxial Overgrowth Transition Structure and Gallium Nitride Semiconductor Structures Fabricated Thereby* and Provisional Application Serial No. 60/109,860 filed November 24, 1998 entitled *Pendeo-Epitaxial Methods of Fabricating Gallium Nitride Semiconductor Layers on Silicon Wafers or Wafers Containing Silicon, and Gallium Nitride Semiconductor Structures Fabricated Thereby*.